

IN THE SPECIFICATION:

Please amend the title as follows:

METHOD OF FABRICATING SEMICONDUCTOR DEVICE HAVING
SEMICONDUCTOR RESISTANCE ELEMENT AND FABRICATION METHOD THEREOF

Please amend the first paragraph as follows:

The present application is a divisional of co-pending U.S. Application No. 09/862,042,
filed on May 21, 2001, which claims priority to Japanese Application No. P2000-153445 filed
May 24, 2000. Both ~~which application is~~ applications are incorporated herein by reference to the
extent permitted by law.